



# BUK763R1-40B

## N-channel TrenchMOS standard level FET

Rev. 03 — 8 February 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a> ; see <a href="#">Figure 1</a>	<a href="#">[1]</a> -	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	300	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	2.6	3.1	mΩ



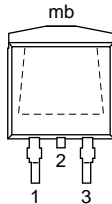
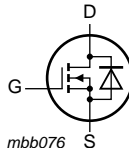
Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped	-	-	1.6	J
Dynamic characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>	-	29	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>		
3	S	source		
mb	D	mounting base; connected to drain		
SOT404 (D2PAK)				

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK763R1-40B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	40	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; see <a href="#">Figure 1</a>	<a href="#">[1]</a> -	75	A
		T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <a href="#">Figure 3</a> ;	<a href="#">[2]</a> -	225	A
		see <a href="#">Figure 1</a>	<a href="#">[1]</a> -	75	A
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <a href="#">Figure 3</a>	-	902	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	300	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C

### Source-drain diode

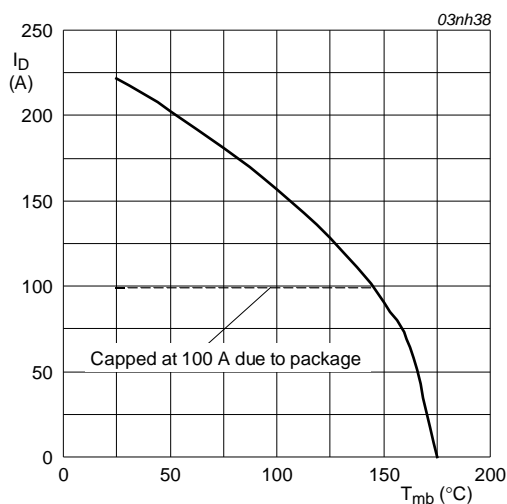
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2] -	225	A
			[1] -	75	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	902	A

### Avalanche ruggedness

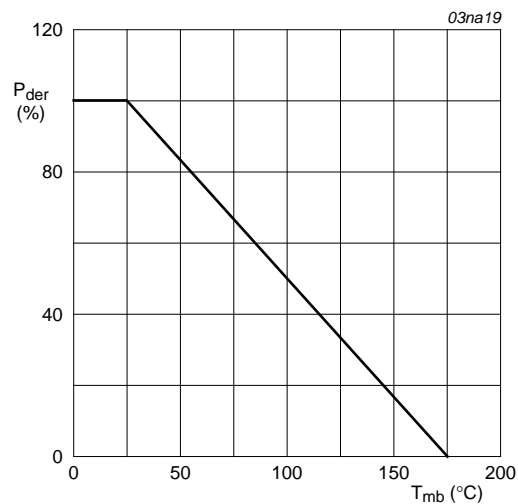
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; unclamped	-	1.6	J
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[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.



**Fig 1. Continuous drain current as a function of mounting base temperature**



**Fig 2. Normalized total power dissipation as a function of mounting base temperature**

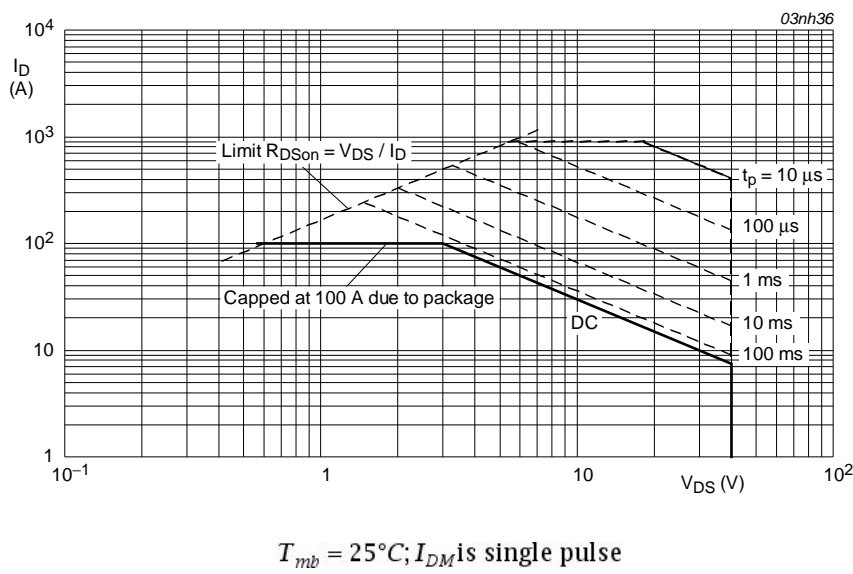


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-board circuit	-	50	-	K/W

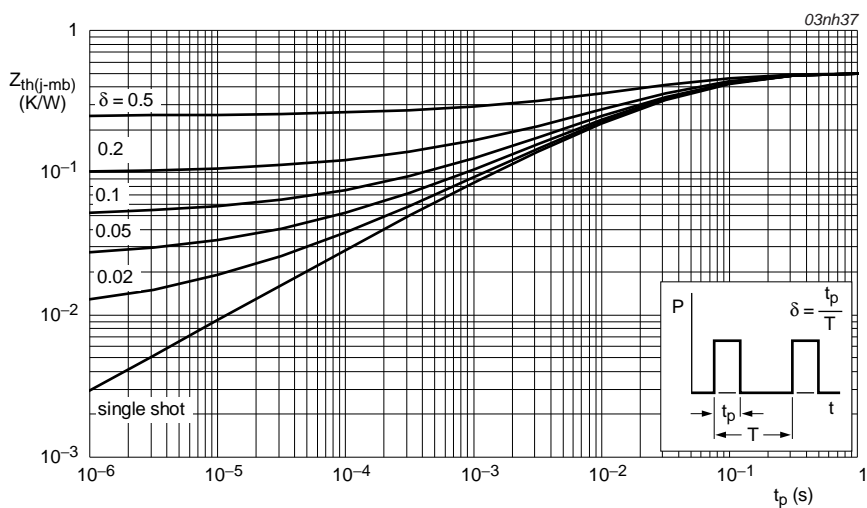


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
		I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <a href="#">Figure 10</a>	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <a href="#">Figure 10</a>	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <a href="#">Figure 10</a>	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	-	5.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	2.6	3.1	mΩ
Dynamic characteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; see <a href="#">Figure 13</a>	-	94	-	nC
Q <sub>GS</sub>	gate-source charge		-	18	-	nC
Q <sub>GD</sub>	gate-drain charge		-	29	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <a href="#">Figure 14</a>	-	5106	6808	pF
C <sub>oss</sub>	output capacitance		-	1390	1667	pF
C <sub>rss</sub>	reverse transfer capacitance		-	530	722	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	38	-	ns
t <sub>r</sub>	rise time		-	82	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	141	-	ns
t <sub>f</sub>	fall time		-	90	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die; T <sub>j</sub> = 25 °C	-	2.5	-	nH
		from drain lead 6 mm from package to center of die; T <sub>j</sub> = 25 °C	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; T <sub>j</sub> = 25 °C	-	7.5	-	nH
Source-drain diode						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 40 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <a href="#">Figure 15</a>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	65	-	ns
Q <sub>r</sub>	recovered charge		-	103	-	nC

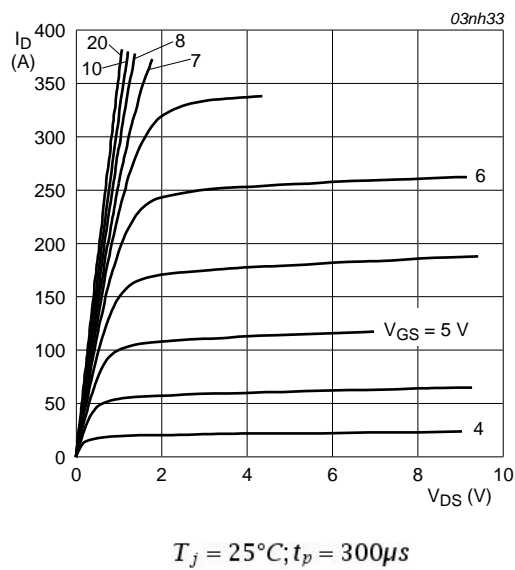


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

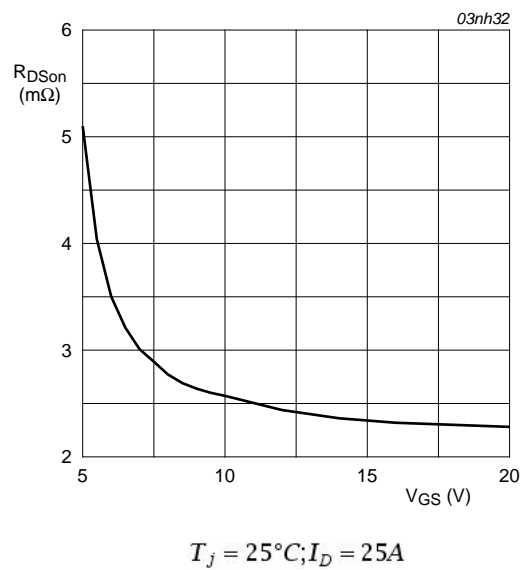


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

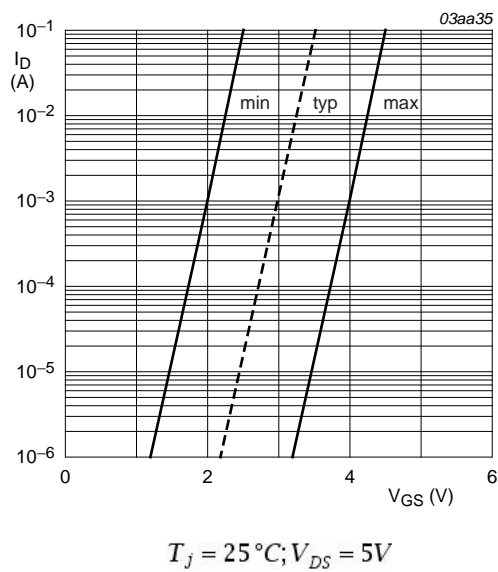


Fig 7. Sub-threshold drain current as a function of gate-source voltage

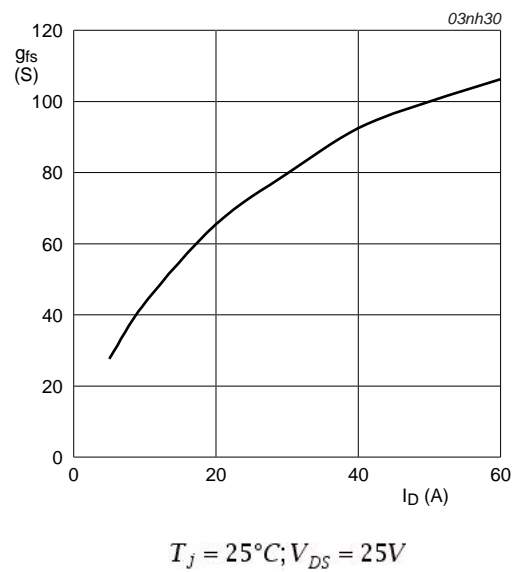


Fig 8. Forward transconductance as a function of drain current; typical values

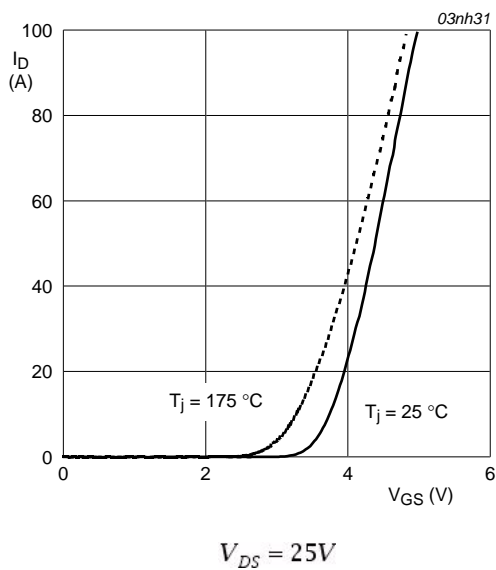


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

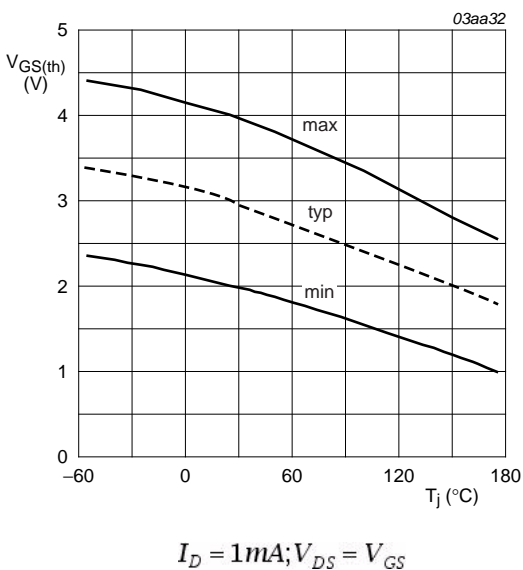


Fig 10. Gate-source threshold voltage as a function of junction temperature

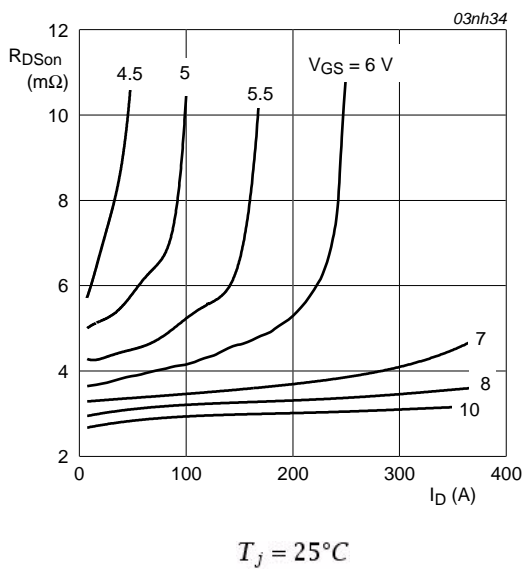


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

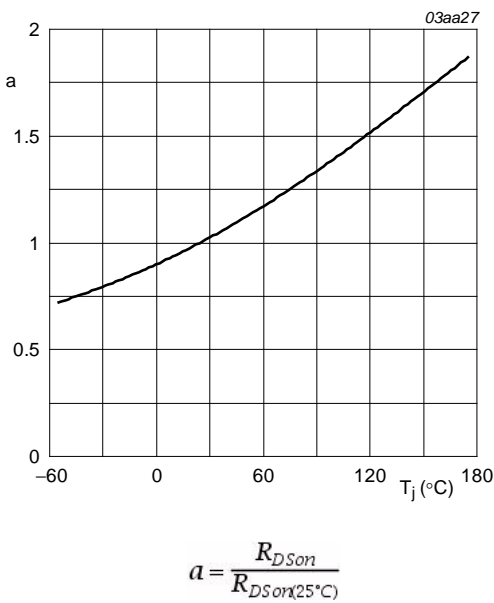
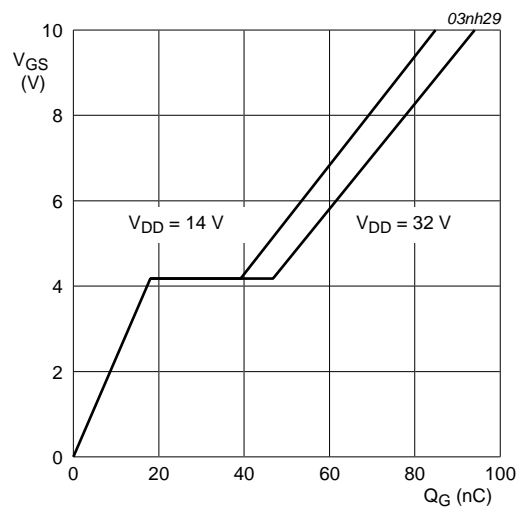
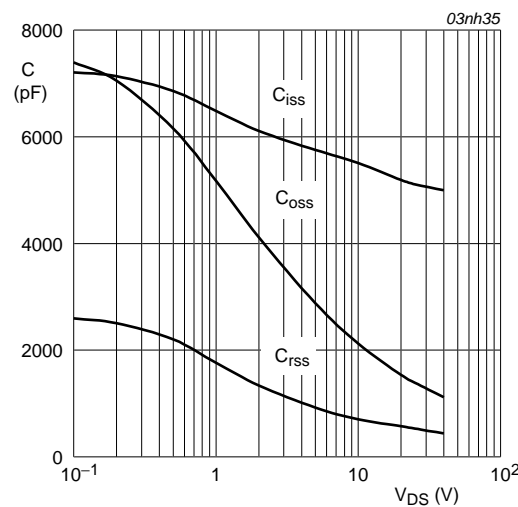


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



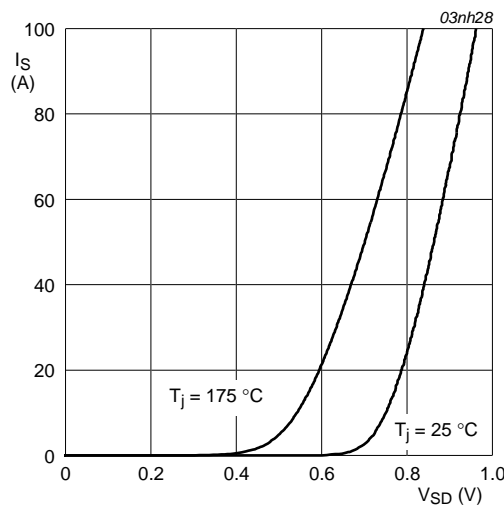
$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

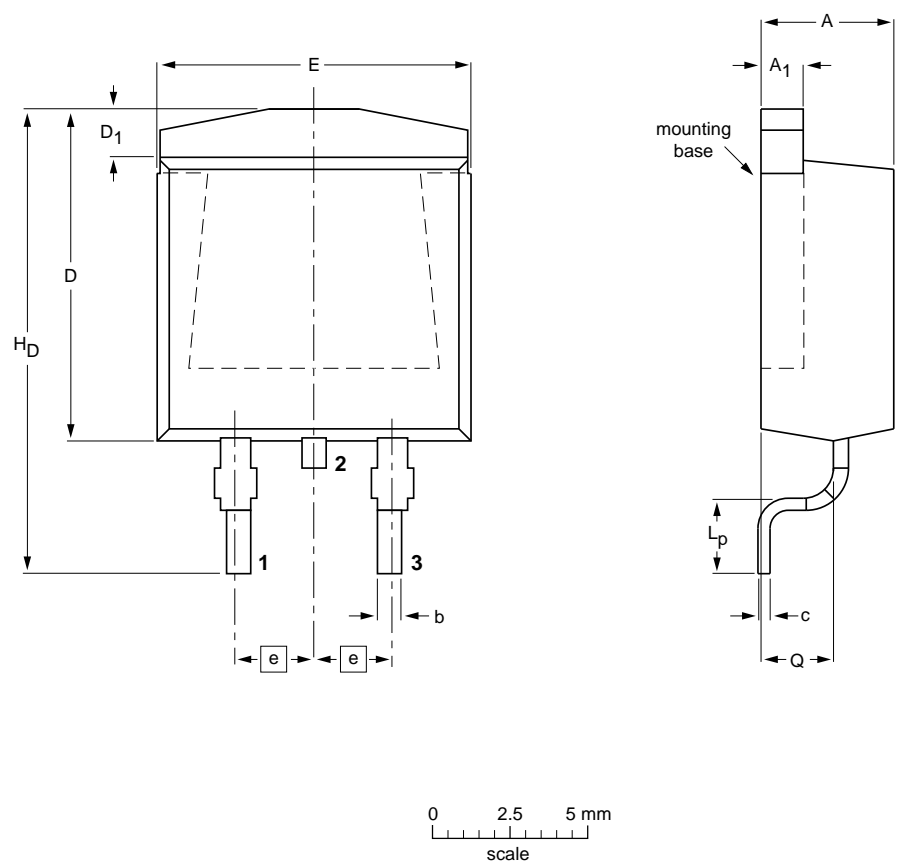
Fig 15. Reverse diode current as a function of reverse diode voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	c	D <sub>max.</sub>	D <sub>1</sub>	E	e	L <sub>p</sub>	H <sub>D</sub>	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

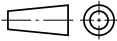
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						05-02-11 06-03-16

Fig 16. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK763R1-40B v.3	20110208	Product data sheet	-	BUK75_763R1_40B v.2
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number BUK763R1-40B separated from data sheet BUK75_763R1_40B v.2.</li></ul>			
BUK75_763R1_40B v.2	20021016	Product data	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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